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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Okuyama et al.
Appl. No.: 10/062,687
Conf. No.: 2178
Filed: January 30, 2002
Title: SEMICONDUCTOR LIGHT-EMITTING DEVICE AND PROCESS FOR
PRODUCING THE SAME
Art Unit: 2811
Examiner: Unknown
Docket No.: 112857-382

Assistant Commissioner for Patents
Washington, DC 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 37 C.F.R. 1.97, and 37 C.F.R. 1.98, Applicants request that a citation and examination of the references cited below, and on the attached PTO-1449 form, copies of which are enclosed, be made during the course of examination of the above-identified application for United States patent.

FOREIGN PATENT DOCUMENTS

<u>Document No.</u>	<u>Date</u>	<u>Country</u>
63-188938	08-04-88	Japan
08-008217	01-12-96	Japan
10-270801	10-09-98	Japan
10-312971	11-24-98	Japan
11-251253	09-17-99	Japan
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2001-085738	03-30-01	Japan
2001-217503	08-10-01	Japan
2002-185660	12-12-02	Japan

OTHER DOCUMENTS

Zheleva et al., *Pendeo-epitaxy – a new approach for lateral growth of gallium nitride structures*, MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).


Kapolnek et al., *Spatial control of InGaN luminescence by MOCVD selective epitaxy*, Journal of Crystal Growth, 189/190 (1998) pp. 83-86.

Applicants look forward to early and favorable consideration of this matter.

Respectfully submitted,

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BY



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